## Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

\* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

# **Panasonic**

MOS FET FC8V22090L

# FC8V22090L

### Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

#### Features

- Low drain-source ON resistance:Rds(on) typ. = 9.5 mΩ(VGS = 4.5 V)
- Built-in gate resistor
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 4E

#### Packaging

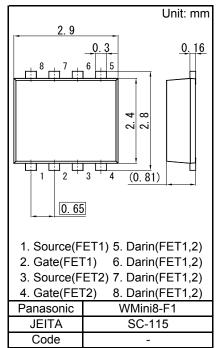
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

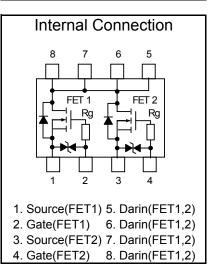
■ Absolute Maximum Ratings Ta = 25 °C								
Parameter		Symbol	Rating	Unit				
Drain-source Voltage		VDS	24	V				
Gate-source Voltage		VGS	±12	V				
Drain Current	DC <sup>*1</sup>	ID1	8	А				
	DC <sup>*2</sup>	ID2	12	Α				
	Pulse *3	IDp	80	А				
Total power dissipation	Ta = 25 °C, DC <sup>*1</sup>	PD1	1.0	W				
	Ta = 25 °C, DC <sup>*2</sup>	PD2	2.0					
	Ta = 25 °C, t = 10 s <sup>*1</sup>	PD3	1.2					
Channel Temperature		Tch	150	°C				
Storage Temperature Range		Tstg	-55 to +150	°C				
Thermal resistance (ch-a)		Rth(ch-a)	125	°C/W				
Nets to Neuroted an ED4 handle (05.4 mm, 05.4 mm, to 0 mm)								

Note \*1 Mounted on FR4 board (  $25.4 \text{ mm} \times 25.4 \text{ mm} \times t0.8 \text{ mm}$  )

Copper foil of the drain portion should have a area of 300mm<sup>2</sup> or more. \*2 Mounted on Ceramic substrate (70 mm × 70 mm × t1.0 mm).

\*3 t = 10  $\mu$ s, Duty Cycle  $\leq$  1 %







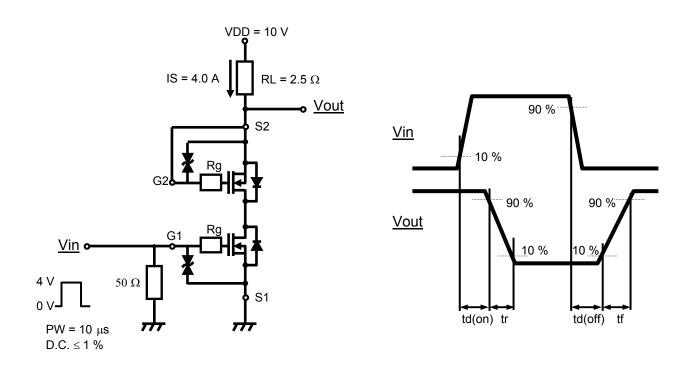
# MOS FET FC8V22090L

■ Electrical Characteristics Ta = 25 °C ± 3 °C

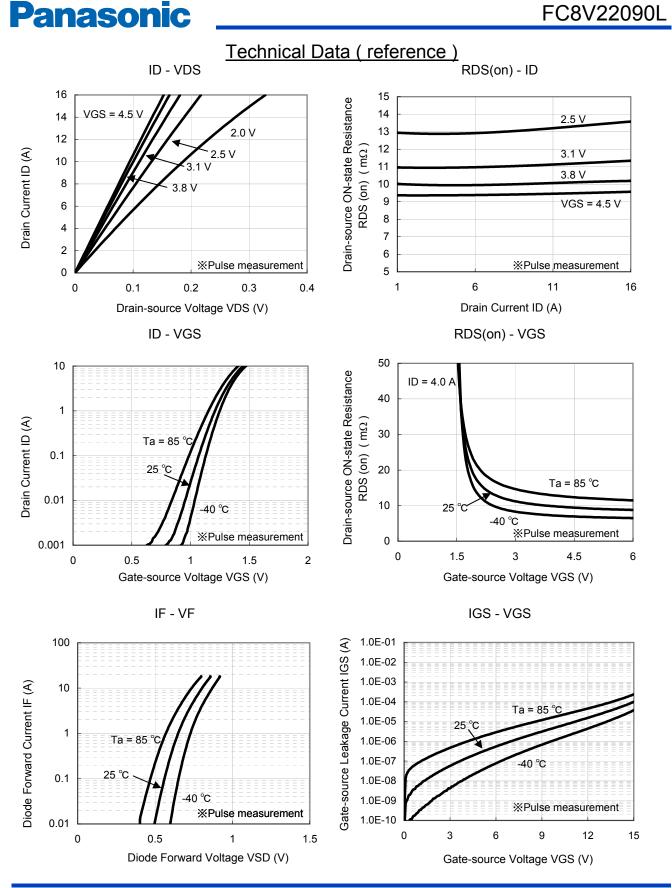
Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	24			V	
Zero Gate Voltage Drain Current	IDSS	VDS = 24 V, VGS = 0 V			1.0	μA	
Gate-source Leakage Current	IGSS	VGS = ±8 V, VSS = 0 V			±10	μA	
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	0.40	0.90	1.4	V	
	RDS(on)1	ID = 4.0 A, VGS = 4.5 V	7.1	9.5	11.8		
Drain-source On-state Resistance	RDS(on)2	ID = 4.0 A, VGS = 3.8 V	7.2	10	12.9	mΩ	
Dialii-source On-state Resistance	RDS(on)3	ID = 4.0 A, VGS = 3.1 V	7.8	11	15.3		
	RDS(on)4	ID = 4.0 A, VGS = 2.5 V	8.5	13.3	20		
Body Diode Forward Voltage	VSD	IF = 8.0 A, VGS = 0 V		0.8	1.2	V	
Input Capacitance *1	Ciss			1230		pF	
Output Capacitance *1	Coss	VDS = 10 V, VGS = 0 V, f = 1 MHz		115			
Reverse Transfer Capacitance *1	Crss			95			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.45			
Rise Time <sup>*1,*2</sup>	tr	ID = 4.0 A		0.75		μs	
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		3		μS	
Fall Time *1,*2	tf	ID = 4.0 A		1.5			
Total Gate Charge <sup>*1</sup>	Qg	VDD = 10 V		11			
Gate-source Charge <sup>*1</sup>	Qgs	VGS = 0 to 4.0 V,		4		nC	
Gate-drain Charge <sup>*1</sup>	Qgd	ID = 8.0 A		2.5			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. \*1 Assured by design

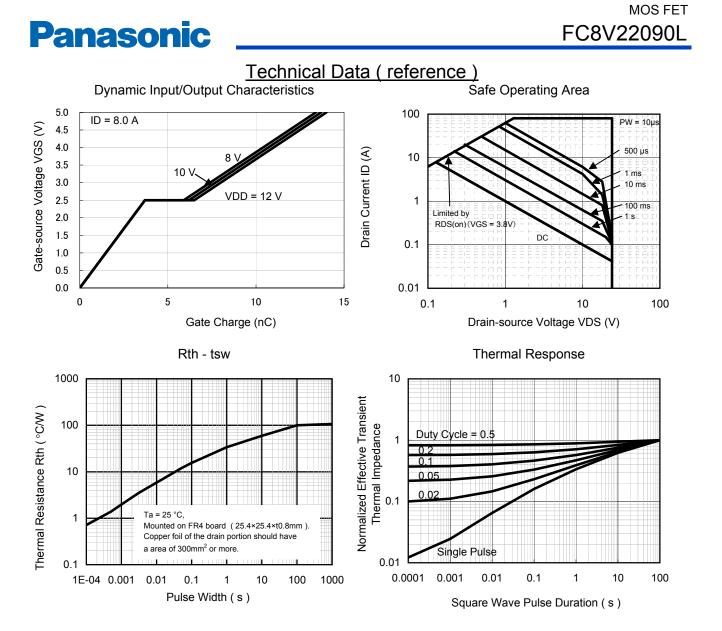
\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



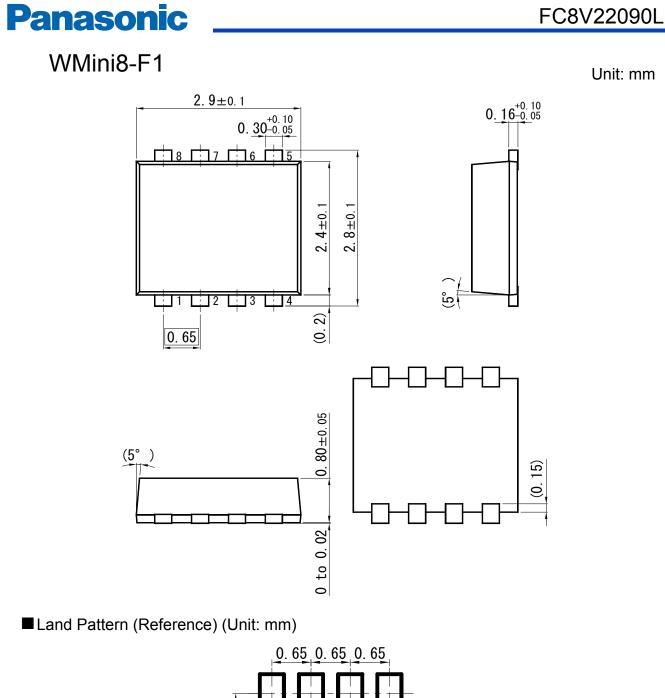
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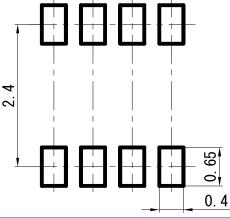


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